

Clean Copy of Claims

The following is a clean copy of amended claim 13.

13. A heterojunction bipolar transistor, comprising:

a collector region;

a SiGe base region;

an emitter stack overlaying said collector region, said emitter stack including an emitter opening filled with T-shaped polysilicon, said T-shaped polysilicon overlaying nitride regions included in said stack; and

one and another extrinsic base regions arranged on respective sides of said emitter stack, said extrinsic base regions being directly aligned with said emitter polysilicon region but not being directly aligned with said emitter opening.